

Kingbright

2.0x1.25mm PHOTOTRANSISTOR

Part Number: APT2012P3BT

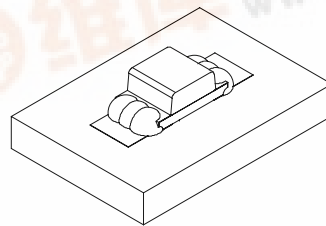
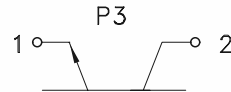
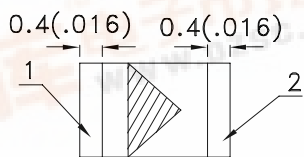
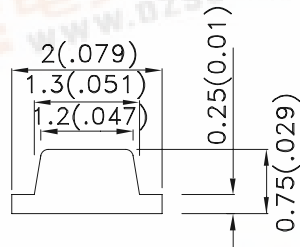
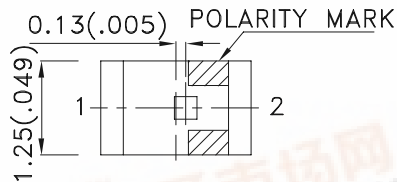
Features

- 2.0mmx1.25mm SMT LED,0.75mm THICKNESS.
- MECHANICALLY AND SPECTRALLY MATCHED TO INFRARED EMITTING LED LAMP.
- BLUE TRANSPARENT LENS.
- PACKAGE: 2000PCS / REEL .
- MOISTURE SENSITIVITY LEVEL : LEVEL 3.
- RoHS COMPLIANT.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.1(0.004)$ unless otherwise noted.
3. Specifications are subject to change without notice.
4. The device has a single mounting surface. The device must be mounted according to the specifications.



Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V _{BR CEO}	Collector-to-Emitter Breakdown Voltage	30			V	I _C =100uA E _e =0mW/c m ²
V _{BR ECO}	Emitter-to-Collector Breakdown Voltage	5			V	I _E =100uA E _e =0mW/c m ²
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage			0.8	V	I _C =2mA E _e =20mW/c m ²
I _{CEO}	Collector Dark Current			100	nA	V _{CE} =10V E _e =0mW/c m ²
T _R	Rise Time (10% to 90%)		15		us	V _{CE} = 5V I _C =1mA R _L =1000Ω
T _F	Fall Time (90% to 10%)		15		us	
I _(ON)	On State Collector Current	0.1	1		mA	V _{CE} = 5V E _e =1mW/c m ² λ=940nm
2θ _{1/2}	Viewing Angle		120		deg	

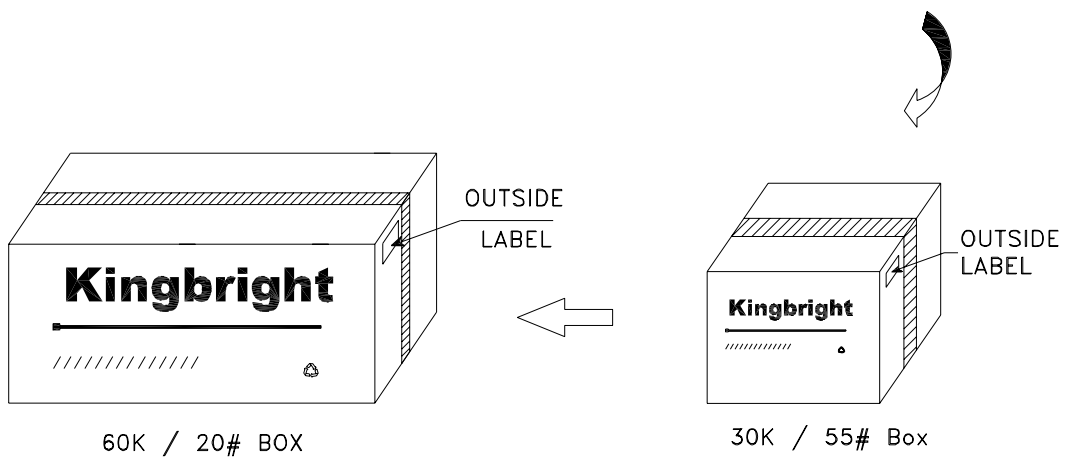
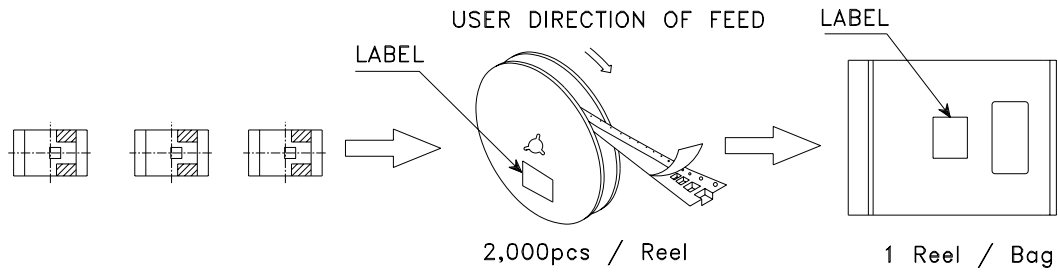
Absolute Maximum Ratings at TA=25°C


Parameter	Max.Ratings
Collector-to-Emitter Voltage	30V
Emitter-to-Collector Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature	-40°C To +85°C
Storage Temperature	-40°C To +85°C

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PACKING & LABEL SPECIFICATIONS

APT2012P3BT



<h1>Kingbright</h1>	
P/NO: APT2012xxx	
QTY: 2,000 pcs	Q.C. Q C XX XX XXXX PASSED
S/N: XXXX	
CODE: XXX	
LOT NO:	
 <small>XXXXXXXXXXXXXXXXXXXXXXXXXXXX</small>	
MADE IN CHINA	RoHS Compliant